## E ects of signs in tunneling m atrix elements on transm ission zeros and phase

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The e ect of the signs in the tunneling matrix elements on the transmission zeros and the transmission phase in transport through a quantum dot is studied. The existence of transmission zeros is determined by both the relative signs and the strength of the tunneling matrix elements for two neighboring energy levels of a dot. The experimentally observed oscillating behavior of the transmission phase over several C oulom b peaks can be explained by a uniform distribution of the relative signs. Based on a simple model of a quantum dot, we present a possible scenario which can give such uniform signs over several conductance peaks. We suggest that the location of the transmission zeros can be identied by inspecting the Fano interference pattern in the linear response conductance of a closed A haronov-Bohm (AB) interferom eter with an embedded quantum dot as a function of the number of electrons in the dot and the AB ux.

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I. IN TRODUCTION

Landauer's scattering theory has been very successful in understanding transport phenom ena in the m esoscopic system s. Electrons, when scattered, experience a phase shift in their wave functions and this phase shift (Friedel phase) is stored in the scattering matrix. Though the transm ission amplitude contains inform ation about both its m agnitude and phase (transm ission phase), the conductance m easures only the absolute value of the transm ission amplitude. Recently a number of experiments have measured the phase shift experienced by electrons passing through a quantum dot, using A haronov-Bohm (AB) interferom eters<sup>1,2,3,4</sup>. The measured phase is not the Friedel phase as we know in bulk systems, but the transmission phase which is the argument of the transm ission amplitude through a quantum dot. In a closed AB interferom eter, the measured phase is constrained to be either 0 or as a consequence of the 0 nsager relations. The phase is observed to jump by at the conductance peaks and rem ains in phase between successive C oulom b peaks<sup>1</sup>.

In order to observe the phase evolution in a quantum dot, an open AB interferom eter sim ilar to the double-slit experiments was devised by Schuster, et.  $al^2$ . The measured phase evolves smoothly by over the Coulomb peaks, which can be expected for resonant tunneling. The transmission phase jumps by somewhere in between two neighboring peaks and remains in phase between successive Coulomb peaks. This unexpected sudden phase jump can be understood in terms of the transmission zeros.<sup>5,6,7</sup> O scillating behavior of the phase { a smooth increase over the Coulomb peaks and a sudden drop in between { is observed over several successive C oulomb peaks.

In this paper we study theoretically the e ects of the signs of the tunneling matrix elements between a quantum dot and two leads on the transmission probability  $T_Q$  of a quantum dot. Silva, O reg, and G efen have recently

shown that the signs of the tunneling matrix elements play a crucial role in determ ining the behavior of the transm ission probability and phase by studying a quantum dot with two resonant levels.8 A number of other works have either explicitly or implicitly addressed the role of the relative sign of the tunneling m atrix elem ents." In this paper, we consider quantum dots with many levels and consider several possible distributions of the signs in the tunneling matrix elements for each energy level in a quantum dot. The e ects of a given distribution of the signs on the transmission phase and zeros is studied. A lthough the distribution of the signs in the tunneling matrix elements is computed for one simple model, the emphasis here is on understanding the general relationship between the transm ission phase and the relative signs of the matrix elements. This can be used, for example, to work backward from experiment to determine the relative signs of the tunneling matrix elements. Not all distributions of the relative signs of the tunneling m atrix elements may be physically realizable. It is still an open question why the phase jump or the transmission zeros show up over the energy range of several C oulom b peaks. Transm ission zeros can arise from the interference between the possible current paths through the multiple energy levels in a dot, and can explain the abrupt phase jumpby .

We nd from our model study that the oscillating behavior in the transmission phase is a result of having the same relative signs in the tunneling matrix elements. Successive transmission zeros in some energy intervalarise when the relative signs in the left and right tunneling matrix elements are the same for all the energy levels lying inside that interval. The well-studied t stub<sup>6,7,10</sup> belongs to this category. The transmission zeros are absent from the interested energy interval when the relative signs oscillate from level to level. In this case, the transmission phase steadily increases by over every peak in T<sub>Q</sub>. The double-barrier well<sup>6,7,10</sup> shows this type of structure in the transmission amplitude. These results are in agreement with those found earlier in two level quantum dots.<sup>8</sup>

B ased on studying several di erent cases for the relative signs of the tunneling matrix elements, we are able to deduce simple rules governing the presence or absence of transmission zeros when the tunneling matrix elements are much smaller than the interlevel energy spacing. In addition depending on the distribution of signs, the transmission probability in an AB interferom – eter with an embedded dot takes on unique shape, especially as a function of the Aharonov-Bohm ux. Thus, com plementary to the direct measurements of the transmission phase in the open AB interferom eter, we suggest that the position of transmission zeros of the quantum dot can be located by inspecting the Fano interference pattern in the linear response conductance.

The rest of this paper is organized as follows. In Sec.II, the modelH am iltonians and the form alism are described. We present our results of our model studies in Sec.III and discuss a particular model for the relative signs of the matrix elements in Sec.IV. Our study is summarized and concluded in Sec.V. In the Appendix, the case of a com plex Fano asymmetry factor in an AB ring geometry is discussed.

### II. MODELAND FORMALISM

To study the e ect of the signs of the tunneling matrix elements between a quantum dot and two leads on the transm ission probability and phase, we consider a quantum dot which is modeled by discrete single-particle energy levels and is connected to two m etallic leads by tunneling. The m etallic leads can accom m odate only one transport channel. The model H am iltonian is given by the equation,  $H = H_0 + H_1$ , where

$$H_{0} = \begin{array}{ccc} X & X & & X \\ H_{0} = & & & p_{k}c_{pk}^{y} & c_{pk} + & E_{i}d_{i}^{y} & d_{i} ; \\ & & & & i \end{array}$$

$$H_{1} = \bigvee_{pk \quad i} V_{pi} C_{pk}^{V} d_{i} + H c:$$
(2)

H<sub>0</sub> is the H am iltonian for the isolated system of two leads and a quantum dot, and H<sub>1</sub> is the tunneling H am iltonian between a dot and two leads.  $E_i = i$   $E_g$  is the energy level of a dot which is shifted by the gate voltage ( $E_g$  is proportional to the gate voltage). The two m etallic leads are conveniently named the left and right leads. The transm ission am plitude for an electron m oving from the left to right lead through the m esoscopic system can be expressed in terms of the m ixed G reen's function,

$$t_{RL}() = 2\frac{G_{RL}^{r}()}{N_{L}N_{R}};$$
 (3)

where N  $_{\rm L\,,R}$  is the density of states in the left (right) lead at the Ferm i level. The m ixed G reen's function G  $_{\rm R\,L}$  is

de ned by

$$i \sim G_{RL}(t;t^0) = \int_{kk^0}^{X} hT c_{Rk}(t) c_{Lk^0}^{V}(t^0) i:$$
 (4)

The transmission amplitude through a quantum dot can be expressed in terms of the Green's function of the dot.

$$\frac{t_{Q}()}{2 p N_{L} N_{R}} = X_{R i} D_{ij}^{r} () V_{jL} :$$
(5)

This transm ission amplitude leads to the familiar expression of the transm ission probability T ( ) =  $j_{R\,L} f$ .

$$T() = 4Trf_{L}D^{r}()_{R}D^{a}()g:$$
 (6)

D  $^{\rm r,a}$  is the retarded (advanced) G reen's function of the dot. The G reen's function of a noninteracting dot is given by the expression,

$$D^{r;a}() = [I E i^{\frac{1}{2}};$$
 (7)

where E<sub>ij</sub> = E<sub>i ij</sub> and <sub>ij</sub> = N<sub>L</sub>V<sub>iL</sub>V<sub>Lj</sub> + N<sub>R</sub>V<sub>iR</sub>V<sub>Rj</sub>. For this noninteracting dot, the transm ission zeros of t<sub>Q</sub> are sensitive to the relative phases of V<sub>Li</sub> and V<sub>Ri</sub>, since t<sub>Q</sub> is the algebraic sum of D<sub>ij</sub> weighted by the tunneling matrix elements.

An Aharonov-Bohm interferom eter is made by introducing direct tunneling between the two leads,

$$H_{2} = \sum_{\substack{k,k^{0} \\ k,k^{0}}}^{X} T_{LR} C_{Lk}^{y} Q_{Rk^{0}} + H x:$$
(8)

The transm ission amplitude through the AB interferom – eterw ith an embedded quantum dot is given by the equation

$$\frac{t_{AB}}{2 P N_{L} N_{R}} = \frac{T_{RL}}{1 +} + \sum_{ij}^{X} V_{Ri} D_{ij}^{r} (N_{jL})$$
(9)

Here =  ${}^{2}N_{L}N_{R} \int T_{LR} \int$  is the dimensionless measure of the direct tunneling rate between the two leads and is related to the direct tunneling probability by  $T_{0} = 4 = (1 + )^{2}$ . The tunneling matrix elements with a tilde can be considered as being renormalized by the direct tunneling:  $\nabla_{iL} = [V_{iL} \quad i \quad V_{iR}N_{R}T_{RL}] = (1 + )$  and  $\nabla_{Ri} = [V_{Ri} \quad i \quad T_{RL}N_{L}V_{Li}] = (1 + )$ . The G reen's function of the dot is also m odi ed by the direct tunneling and the dot's self-energy is given by the expression:

$$\hat{f}_{i;ij} = \sum_{\substack{p=L,R \\ \frac{2N_{L}N_{R}}{1 + \frac{2N_{L}N_{R}}{1 + \frac{2N_{L}N_{R}}{1 + \frac{2N_{L}N_{R}}}}} X V_{ip} T_{pp} V_{pj};$$
(10)

Here the notation L = R and R = L is used. The effect of the A haronov-B ohm ux threading through the AB interferom eter can be taken into consideration by introducing the AB phase = 2 =  $_0$  into the tunneling

m atrix elements as  $V_{R\,i}V_{iL} T_{LR} = \mathbf{j} V_{R\,i}V_{iL} T_{LR} \mathbf{j} \mathbf{e}^{i}$ , where  $_{0} = hc=e$  is the ux quantum.

The behavior of the transm ission phase depends sensitively on the relative phases of the tunneling matrix elements. In the time-reversal symmetric case, an electron's wave functions can be chosen to be real. For a real barrier potential, the tunneling matrix elements  $V_{\rm pi}$  (p = L;R) are thus all real. The signs of tunneling matrix elements can be introduced by the relations:

$$V_{Li} = s_{Li} y_{Li} ; V_{Ri} = s_{Ri} y_{Ri} ;$$
 (11)

Transform ing the electron operator in the dot via

$$d_i ! s_{L_i} d_i ;$$
 (12)

all the phases are ascribed to the right tunneling m atrices. The left tunneling m atrices are all positive,  $V_{\rm L\,i}>0$  for all i's, and

$$V_{Ri} = s_i \mathcal{Y}_{Ri} \mathcal{J}_{Si} = s_{Li} s_{Ri}; \qquad (13)$$

where  $s_i = 1$ . We have no inform ation about the distribution of  $s_i$  at this point. Though the tunneling matrix elements are all assumed to be real, the conclusion remains the same as long as the relative phases between the left and right tunneling matrix elements are real. An overall random phase in the left and right tunneling matrices does not change the physics.

### III. TRANSM ISSION PHASE AND DISTRIBUTION OF RELATIVE SIGNS IN TUNNELING MATRIX ELEMENTS

In this section, we consider several possible distributions of the relative signs in the left and right tunneling m atrix elements and study the behavior of the transm ission zeros and phase. We nd the general rule which governs the relationship between the signs and the transm ission phase. The transm ission probability through a dot takes on m any di erent shapes depending on the distribution of the signs. A closed or unitary AB interferom eter with an embedded quantum dot can thus be an auxiliary experimental probe to measure the transm ission zeros and phase.

Before presenting our results, we brie y comment on the validity of our single-particle approach to a quantum dot. The transmission probability through a quantum dot in a two-term inal con guration is the sum of the G reen's functions of the dot weighted by the tunneling matrix elements [see Eq. (5)]. The poles in the G reen's functions are determ ined by the zeros of the determ inant of  $\mathbb{D}^r$ ]<sup>1</sup>. Though the position of the zeros in the determ inant depends on the relative signs of the tunneling matrix elements, the existence of zeros in the determ inant is not sensitive to the relative signs. On the other hand, the existence of the transmission zeros in t<sub>Q</sub> is sensitively determ ined by the relative signs of the tunneling m atrix elements. At the level of the Hartree approximation, the main e ect of the Coulom b interaction is to to make discrete poles which are separated by the Coulom b interaction plus the di erence in the single-particle energy spectrum. The level broadening is mainly determined by the tunneling into two leads. Since Eq. (5) is valid at the level of the Hartree approximation, we believe the transmission zeros are still determined by the relative signs of the tunneling matrix elements, although we do not consider this case explicitly here.

W e would like to emphasize that our consideration of the distributions of the relative signs in the left and right tunneling m atrix elements do have physical realizations. To obtain the inform ation about the tunneling m atrix elen ents requires the solution of the Schrodinger equation for the entire structure of a quantum dot and two leads. Simplifying the system to the one-dimensional problem, there have been som e approaches to com puting the transm ission am plitude of the quantum dot system . M odeling the quantum dot by a double-barrier well (DBW ) or t stub, plane waves are matched at the boundaries between the quantum dot and the two leads. The structure of the transmission amplitude for the DBW (t stub) is com pletely equivalent to the case of the oscillating (uniform) distribution of the relative signs, as will be discussed below. The stepw ise distribution of the relative signs is also possible for the double-barrier t stub system .

Forourm odel study, we assume the quantum dot is described by a uniform single-particle energy spectrum with energy spacing . The level spacing implicitly includes the e ect of the C oulom b interaction at the H artree approximation level. We keep a nite number of energy levels with i = i where the integer i is constrained i N and N = 50 is chosen in our plots. Ν to The transmission probabilities  $T_0$  (0) of a quantum dot,  $T_{AB}$  (0) of an AB interferom eter at the Fermi energy = 0, and the transmission phase of a quantum dot are computed as a function of the energy shift  $E_q$  by the gate voltage. In most of the presented gures,  $E_{q}$ 4 to 4 . This energy range covers 9 is varied from discrete energy levels of the dot. Unless otherwise noted, we use the same set of the tunneling matrix elements to emphasize the e ects of  $s_i$ 's. The values of  $L_i$ = (<sub>Ri</sub>=)fori= N; N+1; ;N are chosen random ly between 0:01 (0:03) and 0:02 (0:06), respectively, where  $p_{i} = N_{p}V_{iL}V_{Li}$  for p = L; R. W hen the quantum dot is embedded into one arm of an AB interferom eter, the e ect of the AB ux is taken into account by introducing an AB phase into the tunneling matrices. Though the energy spectrum and the tunneling matrix elements of a dot are modied by magnetic elds (see Sec. IV), our presented gures are computed using a rigid energy spectrum and rigid tunneling matrix elements.

To begin we consider the case when all the relative signs are equal, i.e.,  $s_i = 1$  for all i's. The transm ission probability  $T_Q$  of the quantum dot is displayed for this case in Fig. 1 (a).  $T_Q$  has a repeating sequence of zero-pole pairs. The transm ission probability is peaked

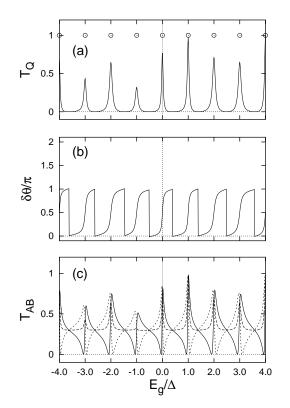


FIG.1: Uniform distribution of relative signs ( $s_i = 1$ ). (a) The transm ission probability  $T_0$  of a quantum dot. Open circles denote the relative signs of the tunneling matrix elements.  $s_i = 1$  when an open circle is located at 1 (0) on the y-direction, respectively. (b) The variation of the transmission phase . (c) W hen the quantum dot is embedded into the A haronov-B ohm interferom eter, the Fano interference pattern shows up in the transmission probability  $T_{AB}$ . The AB phase () dependence of  $T_{AB}$  is displayed ( $T_0 = 0.3$ ): solid line ( = 0), long dashed line ( = 90), and short dashed line ( = 180).

whenever the Ferm ienergy is a ligned with one of discrete energy levels in the dot.  $T_Q$  is zero at the transmission zeros, which lie in between two neighboring transmission peaks or poles. The change in the transmission phase,

, is displayed in Fig. 1 (b). increases by over every transmission peak and jumps by at transmission zeros. shows an oscillating behavior: an increase over poles and a drop at zeros. The transport properties of this quantum dot system are very similar to those of well-studied t stub system  $.6^{7,10}$ 

W hen the quantum dot is embedded in an AB interferom eter, the transm ission probability  $T_{AB}$  shows Fano interference<sup>11</sup> between the direct tunneling and the resonant path through the dot. As shown in Fig. 1 (c), a repeating sequence of zero-pole pairs (solid line) still remains and additional zeros are not generated by the destructive Fano interference. The asymmetric Fano resonance shape in  $T_{AB}$  for each peak are equivalent or \in phase" in the sense that they are modulated in the same

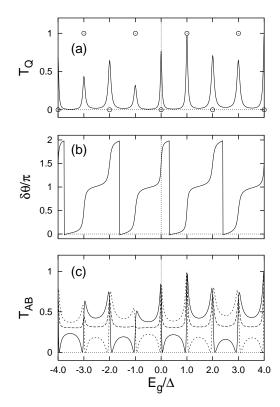


FIG. 2: Oscillating distribution of relative signs (s<sub>i</sub> = (1)<sup>i+1</sup>). The integer i labels the single-particle energy levels in a dot. (a) T<sub>Q</sub> at the Ferm i energy. The meaning of open circles are explained in the caption of Fig. 1. (b) The transmission phase. For display, is folded into the range [0;2] so that the apparent jump of by 2 should be understood as continuous line. (c) T<sub>AB</sub> in an AB ring. Lines are the same as in Fig. 1.

way by the AB ux.  $T_{AB}$  (= 0) has an N -shape structure, and the shape of  $T_{AB}$  is transformed into an inverse N -shape when = 180. The transmission zeros of  $T_{AB}$  lie on the real-energy axis when = n, where n is an integer. For other values of the AB phase, the transmission zeros become e complex. Due to the Onsager relation,  $T_{AB}$  () is equal to  $T_{AB}$  ().

In recent measurem ents of the transmission phase, , of a quantum dot in an open AB interferom eter, oscillating behavior of was observed over several C oulom b peaks. W ithin our model, these experimental features can be explained when the relative signs of the tunneling matrix elements are all equal.

W hen the relative signs of the tunneling matrix elements are oscillating from level to level,  $s_i$  = ( $1^{j^{i+1}}$ , the structure of transmission zeros is drastically modied. There are no transmission zeros in  $T_{\rm Q}$ , but instead  $T_{\rm Q}$  has a series of transmission poles. Since no transmission zeros exist in  $T_{\rm Q}$ , the transmission phase steadily increases by as the energy levels of the dot are scanned by varying E $_{\rm g}$  through the Ferm i level of the leads. The behavior of this quantum dot system is very similar to a

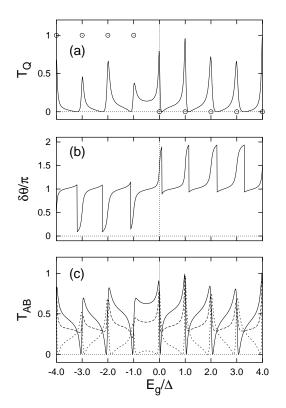


FIG. 3: Stepw ise distribution of relative signs ( $s_i = 1$  for i 1 and  $s_i = 1$  for i 0). (a) The asymmetrical lineshape in  $T_Q$  arises from the combined e ects of the step-wise distribution of relative signs and the interference between multiple energy levels. (b) . One transmission zero is removed in the boundary energy range  $1 < E_g = < 0$ . (c)  $T_{AB}$  in an AB ring. Lines are the same as in Fig. 1.

double-barrier well and double-barrier resonant tunneling system s.<sup>6,7,10</sup>

W hen this quantum dot is inserted into an AB interferom eter, destructive Fano interference generates transm ission zeros in  $T_{AB}$  in an energy interval of  $E_q$  where  $T_{\rm Q}\,$  has no zeros.  $T_{\rm A\,B}\,$  has a repeating sequence of zerozero-pole-pole structure. A lthough the di erence in the  $T_0$  's is not signi cant between the two distributions of  $s_i$ 's in Fig. 1(a) and Fig. 2(a), the shapes of  $T_{AB}$  are quite di erent. In this case TAB consists of a repeating sequence of the structure of M -shape and W -shape when = 0. The M (W)-shape is transformed into the W (M)-shape when = 180. The di erence in Fig.1(c) and Fig. 2 (c) suggests that these two types of distributions in si's can be distinguished by m easuring the linear response conductance GAB in the AB interferom eterwith an embedded quantum dot and by inspecting the shapes of  $G_{AB}$  as a function of the gate voltage and magnetic eld.

W e further explore other possible distribution of  $s_i$ 's. The behavior of  $T_{Q,AB}$  and are displayed in Fig.3 when  $s_i = 1$  for i 1 and s = 1 for i 0. In this stepw ise distribution of the relative signs, the transm ission phase show the expected oscillating behavior due to transmission zeros [see Fig. 1 (b)] in the two energy ranges of uniform relative signs [see Fig. 3 (b)]. However, one transmission zero is removed in the energy interval which lies in between the two energy levels whose signs  $(s_i)$  are opposite. Removal of nergy levels whose signs  $(s_i)$  are opposite. Removal of energy level ( $E_g =$  and  $E_g = 0$  in our model calculation). As displayed in Fig. 3 (a), the shape of  $T_Q$  is now asymmetrical with respect to each peak position. Furtherm ore, the shape of  $T_Q$  in both energy regions of uniform signs is di erent by a \phase" of

in the sense that the AB phase can change the shape of  $T_{AB}$  in one region into that of  $T_{AB}$  in the other, and vice versa [See Fig. 3(c)]. Obviously this phase change in  $T_Q$  stems from the sign ip in the tunneling matrix elements. The absence of one transmission zero in  $T_Q$  is

much more apparent in  $T_{A\,B}$  . We now consider the cases that all the energy levels have the sam e relative signs except for one energy intervalwith the ipped relative signs. The energy levels belonging to this ipped energy interval have the opposite relative signs, s = 1, com pared to all the other levels with s = 1. In Fig. 4 (a) and (b), we study  $T_{Q;AB}$  and when the ipped energy interval consists of only one level, i = 0. Transm ission zeros are rem oved only in the energy range lying in between the two levels with the opposite signs. Since no zeros exist for Eg , the transovereach leveli= m ission phase increases by 1;0;1. The shape of  $T_0$  is similar to the case of uniform distribution of si's except for the rem oval of transm ission zeros. On the other hand  $T_{AB}$  ( = 0) is signi cantly modied in the ipped energy interval. As the number of the ipped levels is increased, transm ission zeros are rem oved only in the energy range lying in between the two levels with opposite signs or in the interface energy range between the ipped interval and the rest. Transm ission zeros and the corresponding phase jum ps persist in between two levels with the same relative signs. The case when the the ipped interval consists of three levels is studied in Fig. 4 (c) and (d). Examination of  $T_{AB}$ reveals that the  $\phase"$  of  $T_{AB}$  is different between the inside and outside of the ipped interval. The interval acts to shift the phase by at the two boundaries, and the shape of  $T_{AB}$  is identical on both sides of the ipped interval.

W hen the line-broadening is much smaller than the interlevel spacing, we can deduce from these results the following rules for the behavior of the transmission zeros. W hen the relative signs are opposite for the two neighboring energy levels, the transmission zero is absent in the energy interval bounded by two levels. W hen the relative signs are the same for two neighboring energy levels, one transmission zero is generated inside the energy interval bounded by two levels. This conclusion can be modiled when one of the linewidth matrix elements is by far larger than the others as will be shown below.

The lineshape in  $T_Q$  (E  $_g$ ) can be asymmetrical depending on the relative signs of the tunneling matrix elements

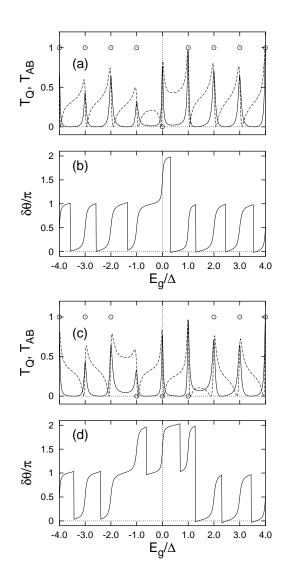


FIG.4:Uniform relative signs (s<sub>i</sub> = 1) except for one ipped sign (s<sub>i</sub> = 1). (a) and (c): Transm ission probabilities  $T_{\rm Q}$  (solid line) and  $T_{\rm A\,B}$  (dashed line). (b) and (d): The transm ission phase of a dot. The jump by 2 should be understood as a continuous line because the phase is de ned to be between 0 and 2 .

and their m agnitude. O ne example of an asymmetrical lineshape is already displayed in Fig. 3 for the stepw ise distribution of relative signs. Another way to make the lineshape of  $T_Q$  asymmetrical is to make one energy level more strongly coupled to the two leads than the other levels. This strongly coupled level is broadened and can act as an elective continuum band to other narrow levels. The interference between the broad level and the narrow levels leads to the asymmetrical Fano lineshape. A typical example is displayed in Fig. 5 when the relative signs in the tunneling matrix elements are equal for all energy levels. A lthough the lineshape in  $T_Q$  is modiled compared to Fig. 1, the transmission zeros for the uniform distribution of signs persist.

In addition to the asym m etrical lineshape, a m ore dra-

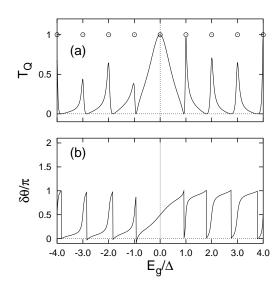


FIG.5: (a) Transm ission probability  $T_Q$  and (b) transm ission phase for a dot when the relative signs are uniform and one energy level is m uch m one strongly coupled to two leads than the other energy levels. Even with the same relative signs for all energy levels, the lineshape is asymmetrical. M odel parameters are the same as in the previous gures except that one of the line broadening parameters,  $_{\rm L,R}$  for i = 0, is chosen to be large:  $_{\rm L0} = _{\rm R0} = = 2$ .

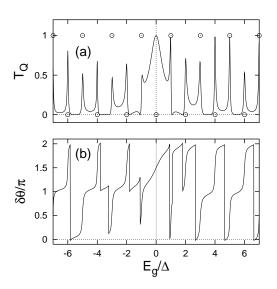


FIG. 6: (a) Transm ission probability  $T_Q$  and (b) transm ission phase for a dot when the relative signs are oscillating from level to level and one energy level is much more strongly coupled to two leads than the other energy levels. Model parameters are the same as in Fig. 5. Note the far-reaching e ect of the strong coupling for one level on the other levels. The jump by 2 in should be understood as a continuous line.

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m atic e ect of Fano interference (see Fig. 6) can occur in the transm ission zeros when the relative signs are oscillating from one level to the next. As shown in Fig. 2, the transm ission zeros are absent for the oscillating distribution of signs when the linew idth is much smaller than the interlevel spacing. Surprisingly, new transm ission zeros are generated due to Fano interference between the broad energy level and the other narrow levels. Note that the strong coupling of one level to the leads is very farreaching and has the same e ect on the structure of the transm ission am plitude as the AB interferom eter.

# IV. MODEL CALCULATION OF RELATIVE SIGNS

In the previous section, we studied the transmission zeros and phase of a quantum dot for several possible distributions of the relative signs in the tunneling matrix elements. A uniform distribution of signs is consistent with recent experimental results. In this section we present a simple scenario which can lead to a uniform distribution of signs.

The single-particle energy-level spectrum in a quantum dot has been inferred by monitoring the position of the Coulom b-regulated conductance peaks as a function of magnetic eld<sup>12</sup>. A fler subtracting the Coulom b interaction from the di erence between two conductance peaks, the single-particle energy spectrum was inferred and well-described by the Fock-D arw in energy levels for some range of magnetic elds. In this section we show that the Fock-D arw in energy spectrum <sup>13,14</sup> of a quantum dot can lead with som e m odest assum ptions to a uniform distribution of the signs of the tunneling matrix elements.

Consider a quantum dot which is de ned in a 2D electron system by the circular harm onic con nem ent potential

$$V_{c}(x;y) = \frac{1}{2}m_{e}!_{0}^{2}(x^{2} + y^{2}): \qquad (14)$$

Here  $m_{\rm e}$  is the electron's mass and  $\sim !_{\,0}$  is the energy scale of the con ning potential. The quantum dot is taken to be weakly coupled by tunneling to two leads which can be described by one transport channel. The tunneling between the two systems is assumed to be weak enough not to modify the electron's wave functions except for broadening the lineshapes. The Coulom b interaction in a dot is treated sem iclassically. W ith these assumptions the single-particle energy spectrum in the presence of perpendicular magnetic elds is given by the Fock-D arw in spectrum ,

$$E(n;m) = (2n + jn j + 1) \sim \frac{1}{2} \sim !_{c};$$
 (15)

and the wave functions are

$$nm$$
 (x;y) =  $N_{nm} e^{im'} j^{j} e^{-2} L_{n}^{jn j} (2)$ : (16)

Here N<sub>nm</sub> =  $\frac{q}{\frac{n!}{a^2(n+jn-j)!}}$  is a norm alization constant, n is the nonnegative integer, and m is an integer. The other variables in this equation are = r=a with a =  $\frac{r}{a} = \frac{r}{10} = \frac{1}{10} + \frac{1}{10} + \frac{1}{10} = \frac{1}{10} + \frac{1}{10}$ 

$$E_N = (N + 1) \sim !_c; N = 2n + jn j;$$
 (17)

Each energy level  $E_N$  is degenerate with  $D_N = N + 1$ , where N = 0;1;2;

We now discuss the structure of the tunneling matrix elements. The tunneling barrier is assumed to be described by a real potential, even in a magnetic eld. To study sim ply oscillating phase-coherent transport, the two leads should accomm odate only one transport channel. Leads with more than one channel will show more complex patterns in the AB oscillations. For a circularly sym m etric quantum dot, the radial part of the wave function determ ines the overallm agnitude of the tunneling matrix elements but plays no role in determining the their phase. The phase of the tunneling m atrix elements is determ ined solely by the angular part of the wave function. For an ideal point contact between the two leads and the quantum dot with one lead at  $\prime = 0$  and the other lead at = , the relative phase between the left and right tunneling matrix elements for the energy level labeled by (n;m) is given by  $e^{im} = (1)^n$ . The ideal point contact condition can be relaxed. If = 0is replaced by  $2 \begin{bmatrix} 1 \\ 1 \end{bmatrix}$  and = is replaced by 2 [  $_{2}$ ; +  $_{2}$ ], then for the constant tunneling over this range of , the relative phase is  $(1)^n$  times the signs of sinm  $_2$ =sinm  $_1$ . As long as  $_{1;2}$ =2, the relative phase is  $(1)^m$  for reasonable values of m.

In the absence of a magnetic eld, any energy level consists of degenerate states with only even m or only odd m . The angular part of wavefunctions can be made real by the appropriate linear combinations of degenerate wavefunctions. The relative signs are still given by  $(1)^n$ . The energy levels of even m and odd m alternate with increasing energy. In a sem iclassical approach to the Coulom b interaction, an electron added to the quantum dot will occupy the single-particle states which are unoccupied and lowest in energy. Until one single particle energy  $level E_N$  is exhausted by 2 (N + 1) electrons (including the spin degeneracy), the relative phases or signs will be equal so that the transmission zeros are generated in between the transmission peaks. W hen the next higher energy  $evel E_{N+1}$  starts to be led, the relative phase is now opposite to that of the lower energy level  $E_{\,\rm N}$  . W hen  $E_{\,\rm g}$  is varied from the last electron  $\,$  lling at  $E_N$  to the rst electron lling at  $E_{N+1}$ , there will not be a transm ission zero. Successive transm ission zeros start to appear again in the transmission amplitude while the energy  $\text{level} E_{N+1}$  is led by electrons. The absence of the transmission zeros is realized only when going from  $E_N$  to  $E_{N+1}$ .

In the presence of a magnetic eld, time-reversal symmetry is broken and the wavefunctions cannot be chosen to be real. The relative signs are still  $(1)^n$  for the state (n;m) if the tunneling barrier potential is real and the electron's wavefunction in the one-channel leads are not modied in the presence of magnetic elds. The transm ission phase will behave in the same way as for B = 0when the magnetic eld is weak enough for level-crossing not to occur. In a strong magnetic eld, energy levelcrossing starts to occur and the distribution of the relative signs is modi ed as well. We believe that keeping track of the relative signs is possible experim entally just like monitoring the Coulomb peaks in the conductance. W hen the magnetic eld is strong enough that only the low est Landau level is led, the energy levels will be ordered with an increasing azim uthal quantum numberm. For this case, the relative signs will oscillate from level to level. However, the spin-degeneracy can double the oscillating period in the relative signs.

### V. CONCLUSION

In this paper we considered several possible distributions of the relative signs in the tunneling matrix elem ents and studied the e ects of these signs on the transm ission zeros and phase. W hen the tunneling matrix elements are much smaller than the interlevel spacing or the distance between the Coulom b peaks, we nd the following general rules governing the relation between the relative signs and the transm ission zeros or phase. W hen the relative signs are opposite for the two neighboring energy levels, a transm ission zero is absent in the energy interval bounded by the two levels. W hen the relative signs are the same for two neighboring energy levels, one transm ission zero is generated inside the energy interval bounded by two levels. Silva, et. al.<sup>8</sup> studied a quantum dot with two energy levels and found these same results. In our work we nd that the above two nules are generally true even in the presence of other energy levels in a dot, as far as the linew idths are much sm aller than the energy level spacing. Based on the above two rules, we can predict the behavior of the transm ission zeros and phase from the distribution of the relative signs. A uniform distribution of signs within some energy interval leads to transmission zeros in between any pair of conductance peaks. The oscillating distribution of signs completely rem oves the transm ission zeros.

W hen the strength of the tunneling matrix elements becomes larger comparable to the interlevel spacing, the above simple rules are modied. One example is when one energy level is coupled much more strongly to the two leads than other levels. W hen the strongly coupled level is broad enough to cover several neighboring energy levels, this broad level can act as the continuum band to the neighboring narrow levels and Fano interference occurs. The Fano interference results in an asymmetrical lineshape as well as the generation of new transmission zeros which are otherwise absent.

Since we did not take into account in full length the

C oulom b interaction between electrons in the quantum dot, some care is needed to apply our theoretical results to the real quantum dots. In the H artree approximation, the C oulom b energy mainly shifts the chemical potential or determ ines the poles of the G reen's function of a dot. W hen the tunneling matrix elements are so sm all that the C oulom b blockade peaks are well separated and narrow, our theory will be relevant to the experiments.

W e have em phasized that the transm ission zeros can be located by inspecting the Fano interference shape in  $T_{AB}$ as a function of the gate voltage and the magnetic eld. The AB phase shifts the transmission zeros o the realenergy axis and m odulates the shape of  $T_{AB}$  . Depending on the existence or the absence of the transmission zeros in  $T_0$ , the variation of  $T_{AB}$  with the gate voltage is quite di erent. There is one experim  $ent^{15}$  in which the linear conductance or  $T_{AB}$  of the AB interferom eter with an em bedded quantum dot was measured. Based on our results [see Fig. 3 (c)], we can conclude that the signs of the tunneling matrix elements are ipped in the gate voltage range  $0.05V < V_{a} < 0V$  of Fig. 1(a) in the work<sup>15</sup> of Kobayashi, et. al. Furtherm ore, all the energy levels covered by the gate voltage  $0.15V < V_q <$ 0:05V seem to have the same relative signs in the tunneling matrix elements. The measured variation<sup>15</sup> of the conductance  $G_{AB}$  in Fig. 4(a) is well reproduced by our  $T_{AB}$  's for a uniform distribution of the relative signs.

Our study shows that the asymmetrical lineshape of  $T_{\rm Q}~(E_{\rm g})$  can result from the interference between the transport channels through the energy levels in a dot. Some experimental groups^{16,17} have observed an asymmetrical lineshape of  $G_{\rm Q}~(E_{\rm g})$  as a function of the gate voltage. This feature may be understood in terms of the interference between multiple energy levels in a dot and the distribution of the relative signs in the tunneling matrix elements.

In sum m ary, we studied the relationship between the transm ission phase and the signs of the tunneling m atrix elements. The behavior of the transm ission zeros and phase is very sensitively dependent on distribution of the relative signs between the left and right tunneling m atrix elements, and on their strength. We suggest that the location of the transm ission zeros can be identied by inspecting the shape of the conductance as a function of the gate voltage in the closed AB interferom eters.

#### A cknow ledgm ents

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### APPENDIX A:COMPLEX FANO FACTOR IN THE AHARONOV-BOHM RING W ITH AN EMBEDDED QUANTUM DOT

A sym m etric Fano lineshapes in the conductance have been observed in transport through the mesoscopic system s.<sup>15,16,17</sup> The AB interferom eter with an embedded quantum dot<sup>15</sup> is one such system. In the main text we have already studied Fano interference patterns in the conductance of an AB ring. In this appendix we are going to show that the com plex Fano factor is closely related to the com plex transm ission zeros in  $t_{AB}$  or the transm ission am plitude of an AB ring. The com plex Fano factor is an oscillatory function of the magnetic elds threading through an AB ring.

As Fano proposed<sup>11</sup>, asymmetric Fano lineshapes arise from the interference between the continuum energy spectrum and one discrete energy level.

$$F(x) = F_1 \frac{(x+q)^2}{x^2+1}$$
: (A1)

Here q is the asymmetric Fano factor and is real in most cases. The Fano resonance is featured with a pair of one dip and one peak structures, which is in direct contrast with the Lorentzian shape of a one peak structure.

To simplify the algebra and to make the physics clear, we consider a model quantum dot which is described by one resonant level. In this case Eq. (9) is simplied as

$$t_{AB} = \frac{\left(\begin{array}{c} d\end{array}\right)^{p} \overline{T_{0}} + \begin{array}{c} -p \overline{g} \cos + i \overline{p} \overline{g} \sin \\ \hline d + p \overline{g} \cos + i \end{array} : (A2)$$

The overall phase is removed from  $t_{A,B}$  and  $_d$  is the resonant energy level. The direct tunneling probability  $T_0$  is given by the expression  $T_0 = 4 = (1 + \gamma^2)$ , where  $= {}^2N_LN_R J_{LR} J$ ,  $= (L + R) = (1 + \gamma)$ , and  $g = 4 {}_LR = (L + R)^2$  with  ${}_{L=R} = N_{L=R} J_{L=R} J$ .

Writing  $Z = d_{p}$ , we can rewrite  $t_{AB}$  in terms of the pole  $Z_{p}$  and the zero  $Z_{z}$  as

$$t_{AB} = \frac{p}{T_0} \frac{Z}{Z} \frac{Z_z}{Z_p} : \qquad (A3)$$

This zero-pole pair is given by the expressions,

$$Z_{p} = \frac{-p}{r} \frac{-p}{-p} \cos i; \qquad (A 4a)$$

$$Z_z = \frac{g}{T_0} [\cos + i\sin ]: \quad (A 4b)$$

Writing  $x = (d_{d}) = \overline{d}$ , the transmission probability  $T_{AB} = \overline{d}_{AB} + \overline{d}$  becomes

$$T_{AB} = T_0 \frac{jx + q()j}{(x + p - g \cos j^2 + 1)};$$
 (A5)

where q() =  $Z_z$ () =  $q - \frac{q}{T_0} e^i$  is the complex asymm etric Fano factor.  $T_{AB}$  is of the same form as Eq. (A1) except that the asym m etric Fano factor is now a complex num ber depending on the AB phase . The asym m etric Fano factor is proportional to the transm ission zero of the AB ring. The absolute m agnitude of q,  $jqj = -\frac{q}{T_0}$ , is independent of the m agnetic eld in the case of one resonant levelm odel.

W hen the quantum dot is modeled by multiple resonant levels, the basic features of one resonant levelm odel are not modi ed. The complex transmission zeros in  $t_{A\,B}$  become purely real when = n with an integer n. Though the imaginary part of the zeros in  $t_{A\,B}$  is still sinusoidal as a function of , its functional form is not given by the form sin  $\stackrel{7}{.}$  The absolute value of the complex Fano factor in this case is weakly dependent on magnetic eld.

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